



FGL40N120AN

1200V NPT IGBT



July 2007

Features

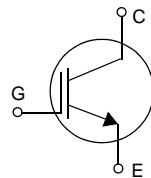
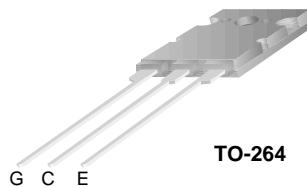
- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.6 \text{ V}$ @ $I_C = 40\text{A}$
- High input impedance

Applications

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

Description

Employing NPT technology, Fairchild's AN series of IGBTs provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).



Absolute Maximum Ratings

Symbol	Parameter	FGL40N120AN	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 25	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	64	A
	Collector Current @ $T_C = 100^\circ\text{C}$	40	A
$I_{CM(1)}$	Pulsed Collector Current	160	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	500	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	200	W
SCWT	Short Circuit Withstand Time, $V_{CE} = 600\text{V}$, $V_{GE} = 15\text{V}$, $T_C = 125^\circ\text{C}$	10	μs
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 seconds	300	$^\circ\text{C}$

Notes:

(1) Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.25	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	25	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGL40N120AN	FGL40N120AN	TO-264	-	-	25

Electrical Characteristics of the IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 1\text{mA}$	1200	--	--	V
$BV_{CES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 1\text{mA}$	--	0.6	--	$\text{V}/^\circ\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{V}$	--	--	1	mA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{V}$	--	--	± 250	nA
On Characteristics						
$V_{GE(\text{th})}$	G-E Threshold Voltage	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.5	5.5	7.5	V
$V_{CE(\text{sat})}$	Collector to Emitter Saturation Voltage	$I_C = 40\text{A}, V_{GE} = 15\text{V}$	--	2.6	3.2	V
		$I_C = 40\text{A}, V_{GE} = 15\text{V}, T_C = 125^\circ\text{C}$	--	2.9	--	V
		$I_C = 64\text{A}, V_{GE} = 15\text{V}$	--	3.15	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{V}, V_{GE} = 0\text{V}$ $f = 1\text{MHz}$	--	3200	--	pF
C_{oes}	Output Capacitance		--	370	--	pF
C_{res}	Reverse Transfer Capacitance		--	125	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600\text{V}, I_C = 40\text{A}, R_G = 5\Omega, V_{GE} = 15\text{V}, \text{Inductive Load}, T_C = 25^\circ\text{C}$	--	15	--	ns
t_r	Rise Time		--	20	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	--	ns
t_f	Fall Time		--	40	80	ns
E_{on}	Turn-On Switching Loss		--	2.3	3.45	mJ
E_{off}	Turn-Off Switching Loss		--	1.1	1.65	mJ
E_{ts}	Total Switching Loss		--	3.4	5.1	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600\text{V}, I_C = 40\text{A}, R_G = 5\Omega, V_{GE} = 15\text{V}, \text{Inductive Load}, T_C = 125^\circ\text{C}$	--	20	--	ns
t_r	Rise Time		--	25	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	120	--	ns
t_f	Fall Time		--	45	--	ns
E_{on}	Turn-On Switching Loss		--	2.5	--	mJ
E_{off}	Turn-Off Switching Loss		--	1.8	--	mJ
E_{ts}	Total Switching Loss		--	4.3	--	mJ
Q_g	Total Gate charge	$V_{CE} = 600\text{V}, I_C = 40\text{A}, V_{GE} = 15\text{V}$	--	220	330	nC
Q_{ge}	Gate-Emitter Charge		--	25	38	nC
Q_{gc}	Gate-Collector Charge		--	130	195	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

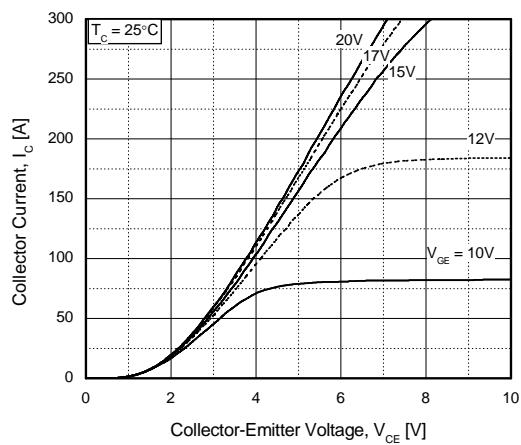


Figure 2. Typical Saturation Voltage Characteristics

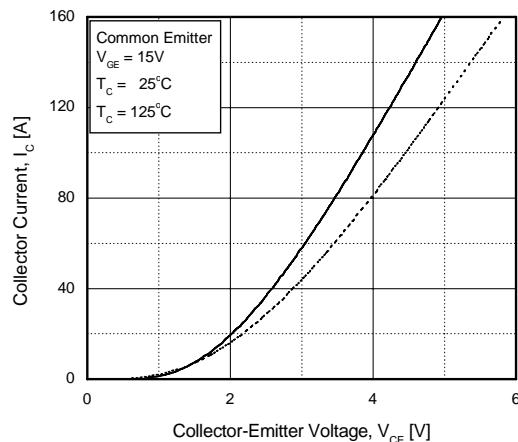


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

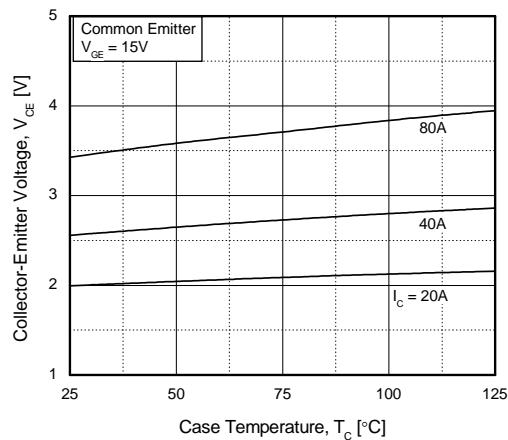


Figure 4. Load Current vs. Frequency

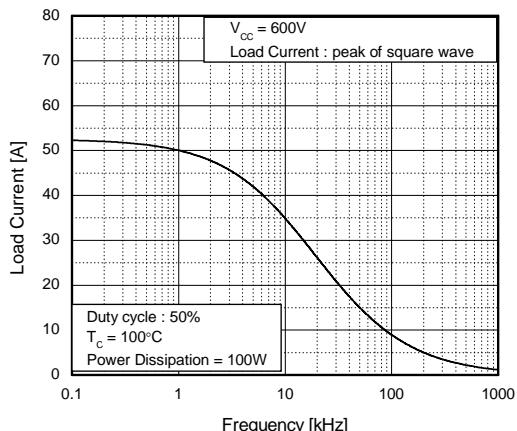


Figure 5. Saturation Voltage vs. V_{GE}

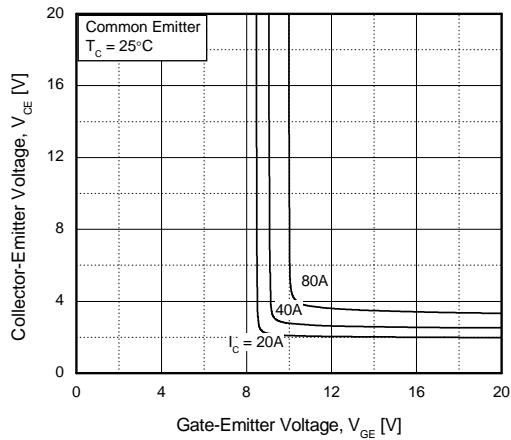
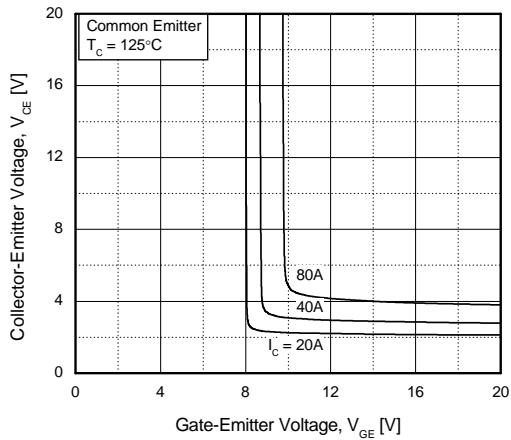


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

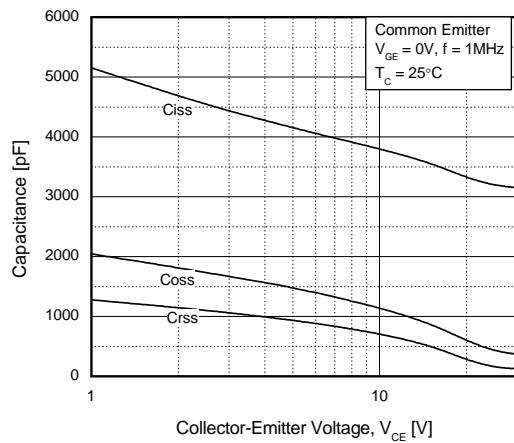


Figure 8. Turn-On Characteristics vs. Gate Resistance

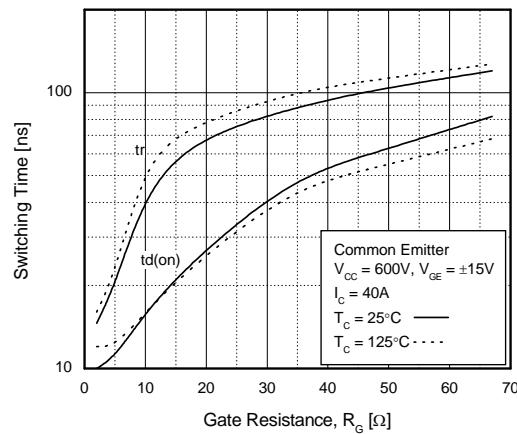


Figure 9. Turn-Off Characteristics vs. Gate Resistance

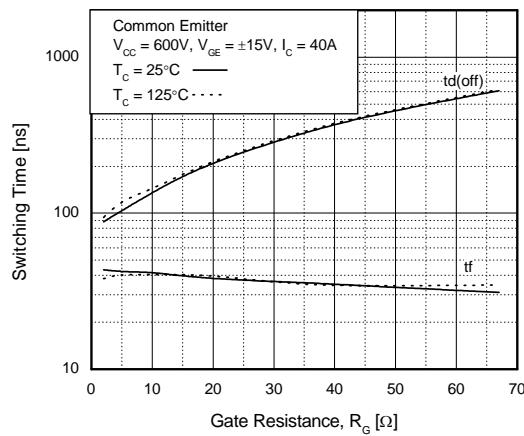


Figure 10. Switching Loss vs. Gate Resistance

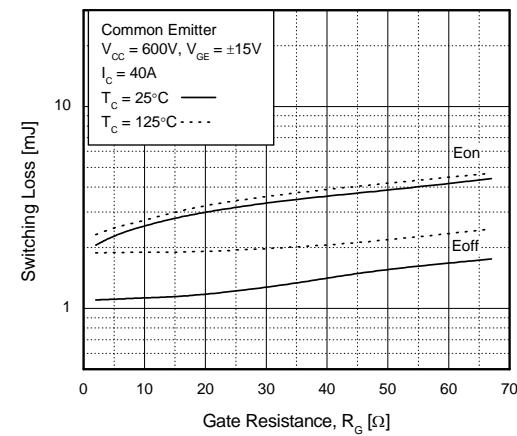


Figure 11. Turn-On Characteristics vs. Collector Current

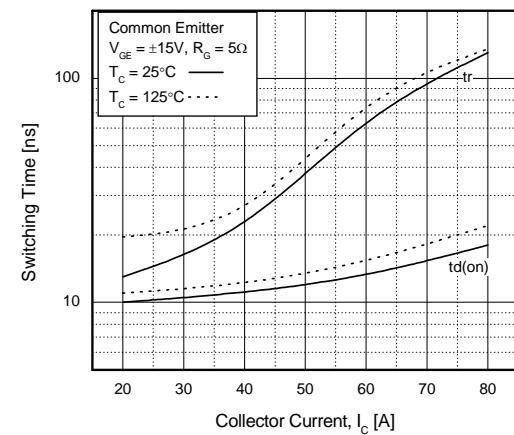
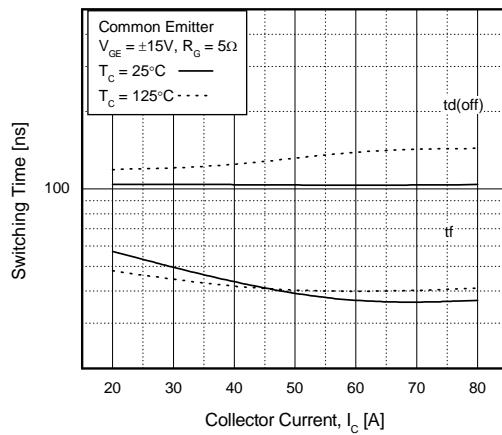


Figure 12. Turn-Off Characteristics vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

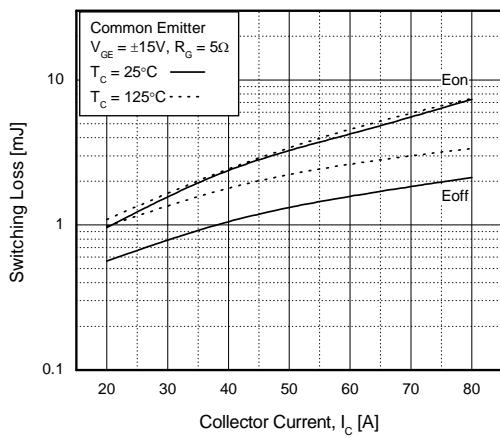


Figure 14. Gate Charge Characteristics

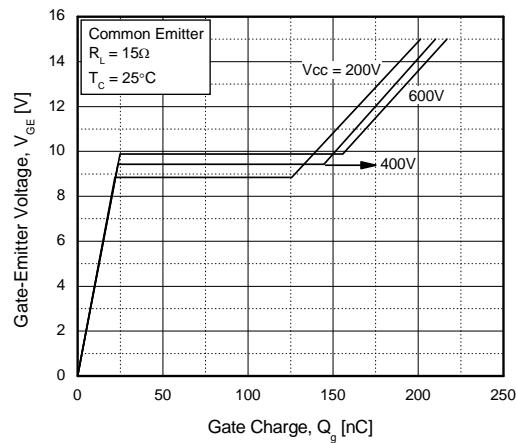


Figure 15. SOA Characteristics

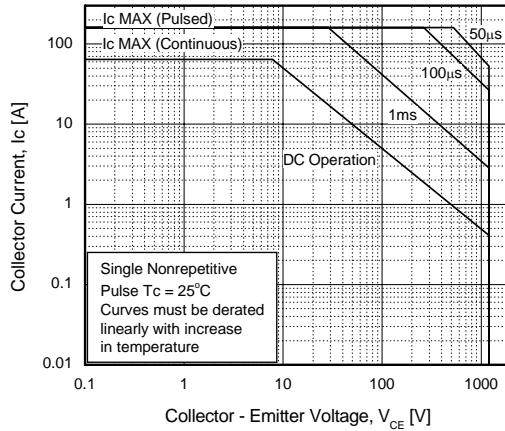


Figure 16. Turn-Off SOA

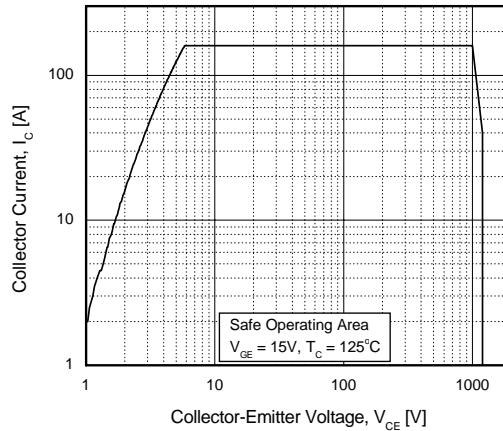
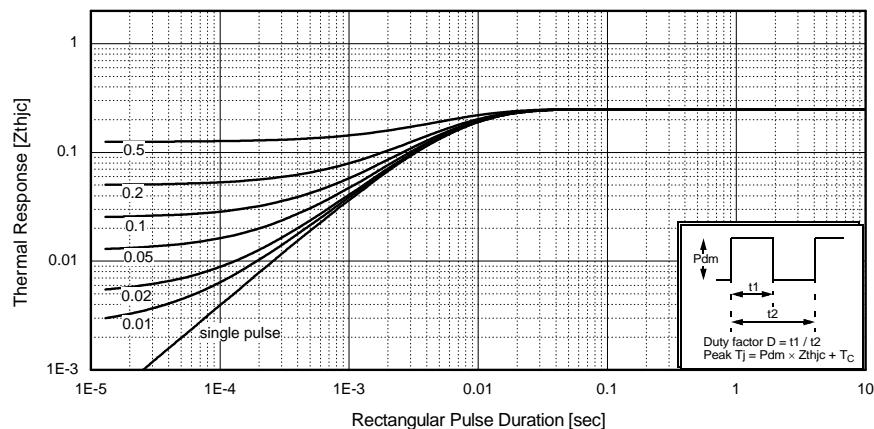
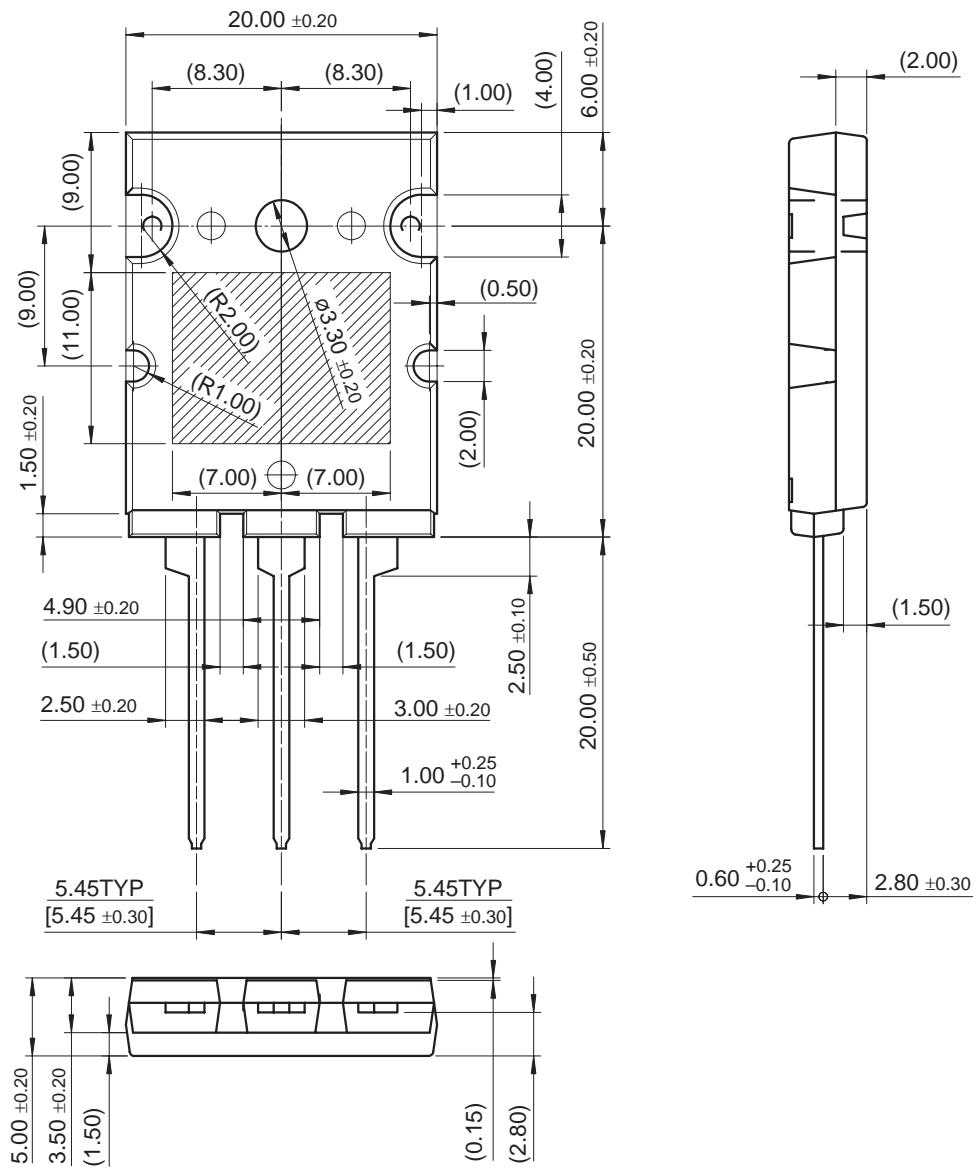


Figure 17. Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-264



Dimensions in Millimeters



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Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

➤ Customer Service :

Email service@ameya360.com

➤ Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com